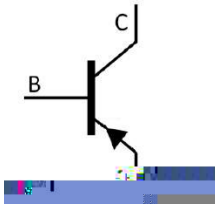
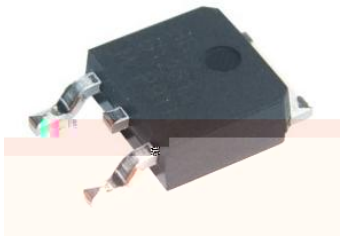
WR0585 ṂṂ Ḷ SQS ÆṀ ч s ‖ ㄱ Silicon PNP transistor in a TO-252 Plastic Package.

Ӈ V_{CEO} ı ᴈ ɔ ╚ щ `
Low Collector Emitter Saturation Voltage, High Current Gain.

ᵹ ˍ ḭ ı ' ѽ ᶻ ı ṇ ɔ ╚ ᴈ ѡ Ầ ʜ
Low power audio amplifier,Low current, high speed switching applications.



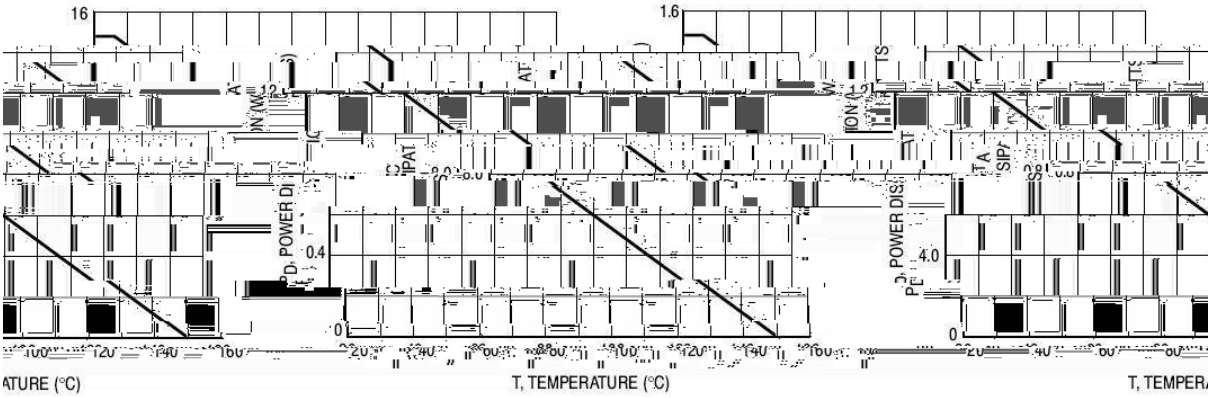


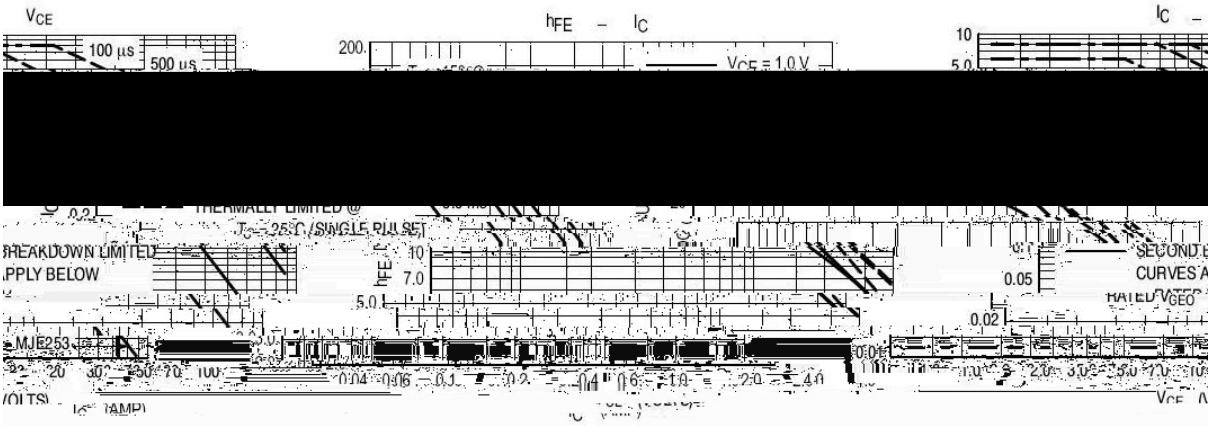
PIN1 χ Base PIN 2,4 χ Collector PIN 3 χ Emitter

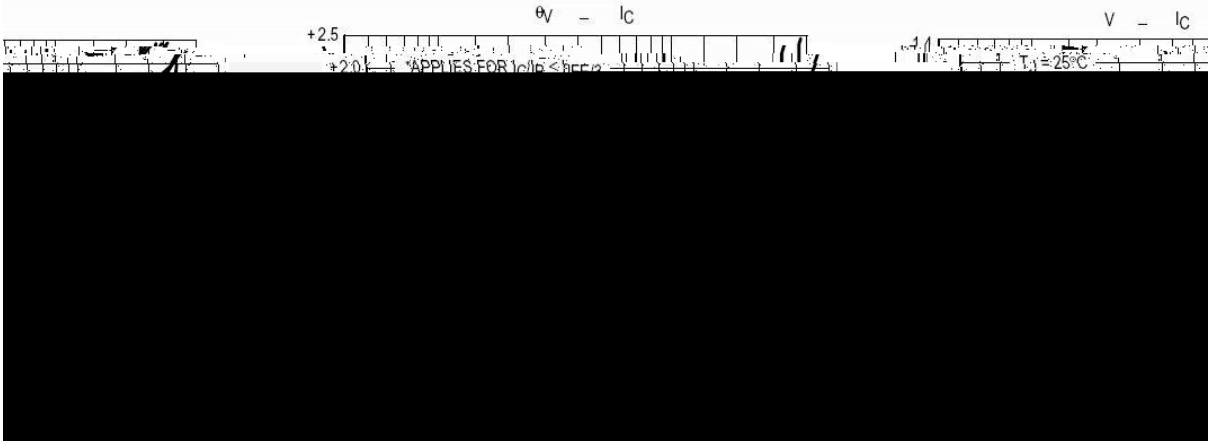
ծ м ㄱ ب ˝ See Marking Instructions.

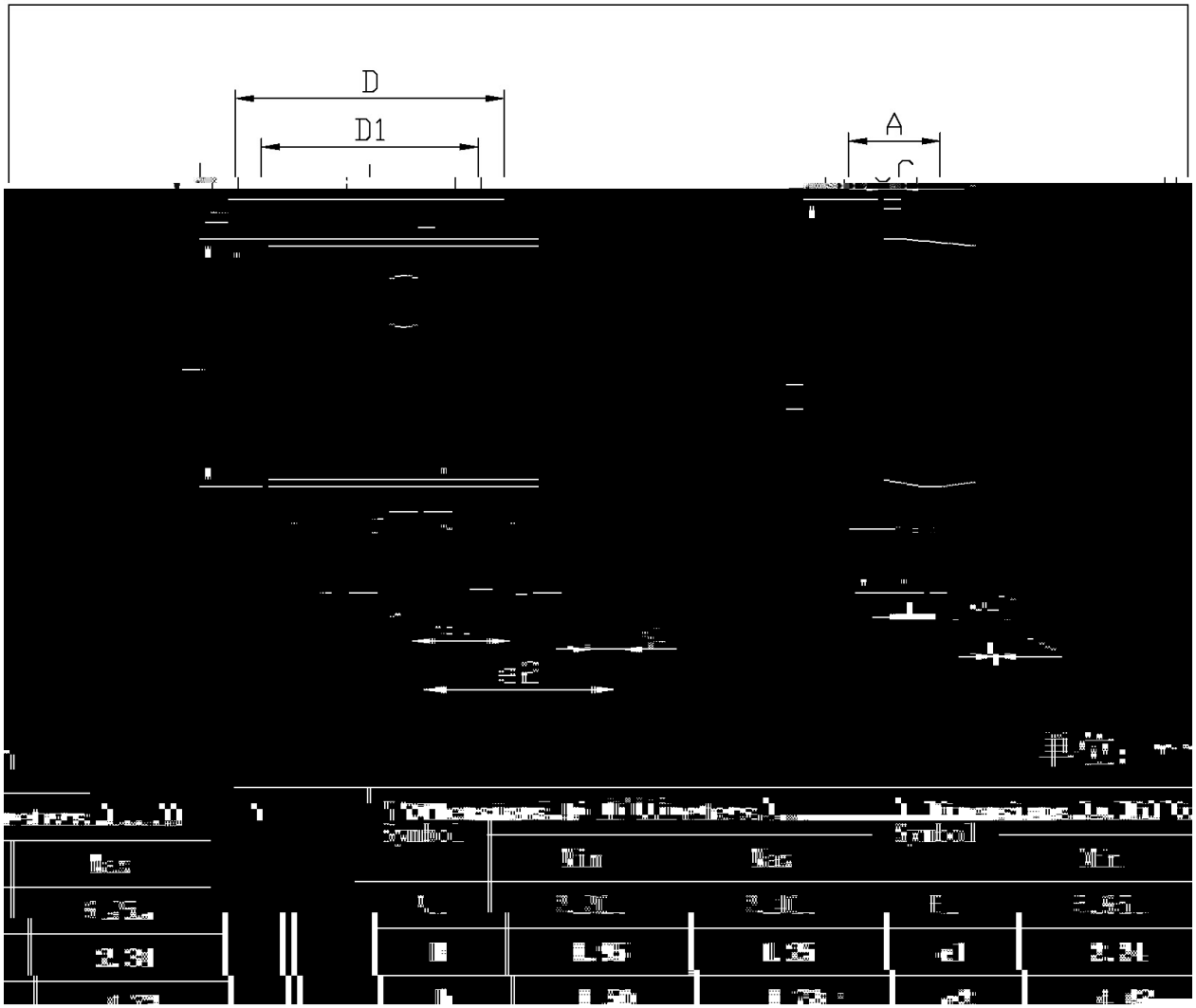
v ̈Ω Parameter	ϒ N Symbol	̈Ω Ö Rating	D Ч Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-7.0	V
Collector Current - Continuous	$I_{C(1)}$	-4.0	A
Peak Collector Current - Continuous	$I_{C(2)}$	-8.0	A
Base Current - Continuous	I_B	-10	A
Collector Power Dissipation	P_D	1.4	W
Collector Power Dissipation	P_D(Tc=25)	12.5	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

v ̈Ω Parameter	ϒ N Symbol	Ш :ϯ Ţ Test Conditions	ώ ṇ Ö Min	Ɛ ʒ Ö Typ	ώ ² Ö Max	D Ч Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-10mA I_B=0	-100			V
Collector Cut-Off Current	$I_{CBO(1)}$	V_{CB}=-100V I_E=0			-0.1	A
	$I_{CBO(2)}$	V_{CE}=-100V Tc=125			-0.1	mA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-7.0V I_C=0			-0.1	A
DC Current Gain	$h_{FE(1)}$	V_{CE}=-1.0V I_C=-200mA	40		180	
	$h_{FE(2)}$	V_{CE}=-1.0V I_C=-1.0A	15			
Collector to Emitter Saturation Voltage	$V_{CE(sat)\ (1)}$	I_C=-500mA I_B=-50mA			-0.3	V
	$V_{CE(sat)\ (2)}$	I_C=-1.0A I_B=-100mA			-0.6	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=-2.0A I_B=-200mA			-1.8	V
Base to Emitter On Voltage	$V_{BE(on)}$	V_{CE}=-1.0V I_C=-500mA			-1.5	V
Current- Gain Bandwidth Product	f_T	V_{CE}=-10V I_C=-100mA	40			MHz
Output Capacitance	C_{ob}	V_{CB}=-10V f=0.1MHz			50	pF


16
1.6
0.4
4.0
0
T, TEMPERATURE (°C)

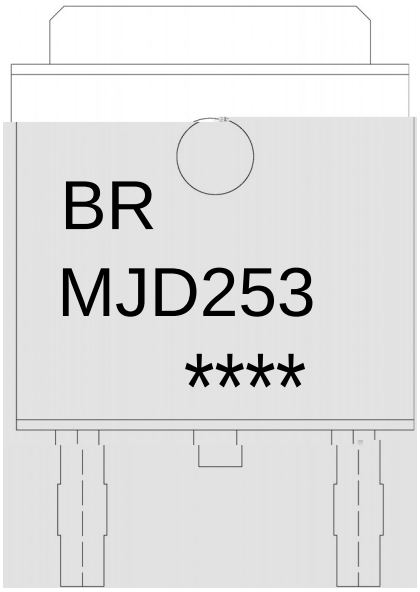

100 µs
500 µs
200
10
7.0
5.0
0.05
0.02
MJE253


+2.5
+2.0
T_J = 25°C



Symbol	Min	Max	Symbol	Min
		L5	L3		

TO-252

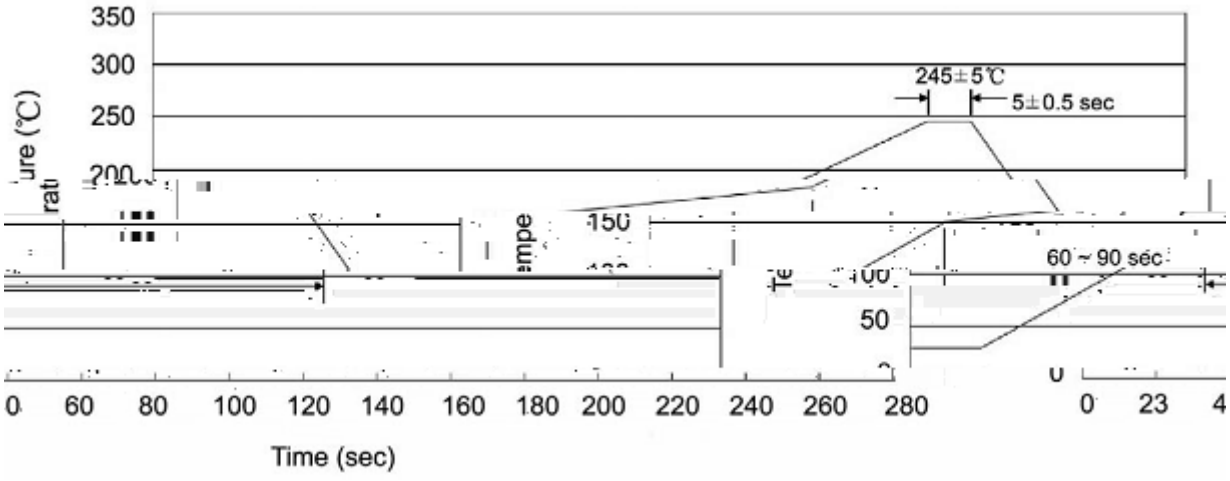


͡ ˝ χ	
BR χ	ѭ ϗ и Ґђ
P M G586 χ	ѭ ғ β ʒ ɴ
---- χ	ѭ ɨ ғ ӈ ɴ Ґђ ɪ ҿ ɨ ғ ӈ ɴ Ψ ҏ

Note:

BR:	Company Code
MJD253:	Product Type.
****:	Lot No. Code, code change with Lot No.

Temperature Profile for IR Reflow Soldering(Pb-Free)



ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ł ı ˋH ڑ 60 Ḱ 90sec;

2 Š Ë □ ỷ 245 ° 5 ł ı ˋH ڑ ˋY ﾊ ㎞ 5 ° 0.5sec;

3 ì ˙ ﾘ ˛ ɔ ﻉ ỷ ㎞ 2 Ḱ 10 ł /sec.

Note:

1.Preheating:25~150 ł , Time:60~90sec.

2.Peak Temp.:245 ° 5 ł , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ł /sec.

□ ỷ χ 260 ° 5 ł ˋH ڑ χ 10 ° 1 sec. Temp.:260±5 Time:10±1 sec

ɔ ` ﾔ Ł / REEL

Package Type	Units					Dimension		(unit mm^3)
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
TO-252	2,500	2	5,000	5	25,000	13 ×16	360×360×50	385×257×392

s